20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)\ max}$	I_D T_A = +25°C
-20V	95mΩ @ V_{GS} = -4.5V	3.0A
	130mΩ @ V_{GS} = -2.5V	2.5A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Analog Switch

Features and Benefits

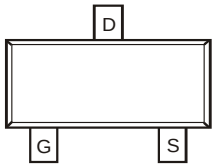
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

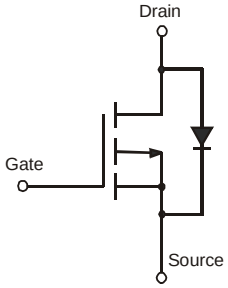
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.0072 grams (approximate)

SOT23

Top View



Pin Configuration



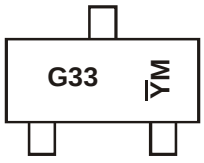
Internal Schematic

Ordering Information (Note 4)

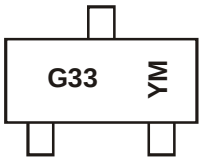
Part Number	Case	Packaging
DMG3413L-7	SOT23	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

G33 = Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
$\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site)
Y or $\overline{Y}$ = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017	2018
Code	X	Y	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	184	°C/W
	t<10s		115	
Total Power Dissipation (Note 6)		P_D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	94	°C/W
	t<10s		61	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	25	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	3.0 2.4	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	3.7 2.9	A
Continuous Drain Current (Note 6) V_{GS} = -2.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.5 2.0	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	3.2 2.5	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	1.9	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	20	A

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	µA	V_{DS} = -16V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.6	-0.55	-1.3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	73	95	mΩ	V_{GS} = -4.5V, I_D = -3.0A
			95	130		V_{GS} = -2.5V, I_D = -2.6A
			146	190		V_{GS} = -1.8V, I_D = -1A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	8	-	S	V_{DS} = -5V, I_D = -3A
Diode Forward Voltage	V_{SD}	—	-0.8	-1.25	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	857	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	54	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	49	—	pF	
Gate Resistnace	R_g	—	12.3	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	9.0	—	nC	V_{GS} = -4.5V, V_{DS} = -15V, I_D = -4A
Gate-Source Charge	Q_{gs}	—	1.6	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.1	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	9.7	—	ns	V_{DS} = -15V, V_{GS} = -10V, R_L = 15Ω, R_G = 6.0Ω, I_D = -1A
Turn-On Rise Time	t_r	—	17.7	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	268.8	—	ns	
Turn-Off Fall Time	t_f	—	64.2	—	ns	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
7 .Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

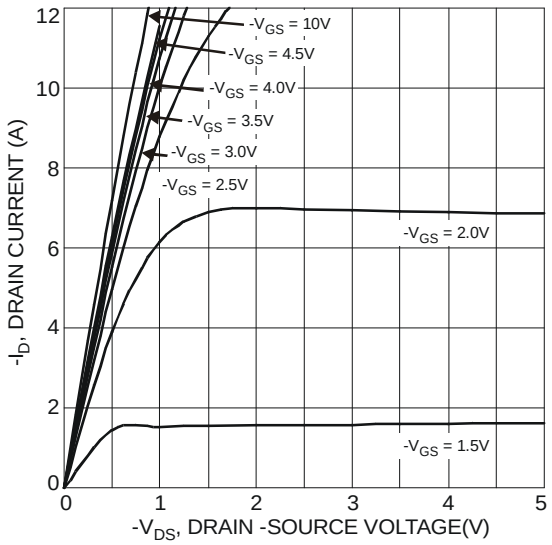


Fig. 1 Typical Output Characteristics

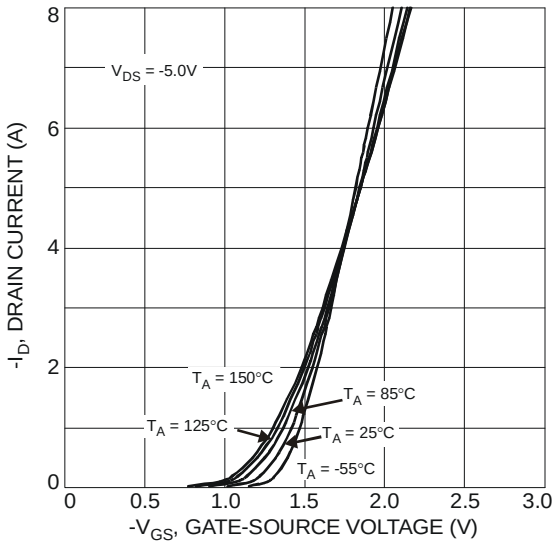


Fig. 2 Typical Transfer Characteristics

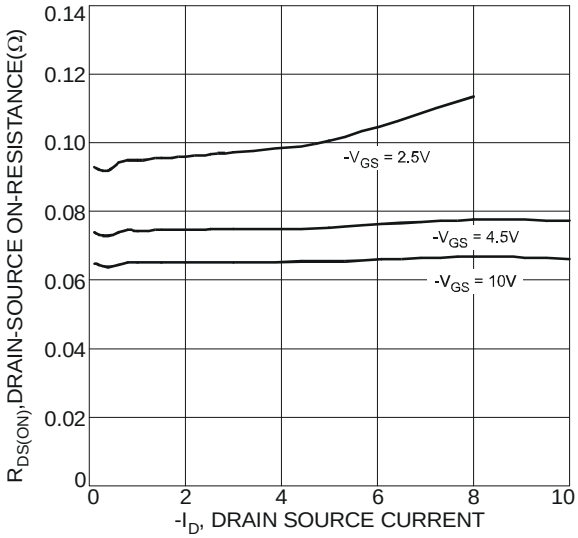


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

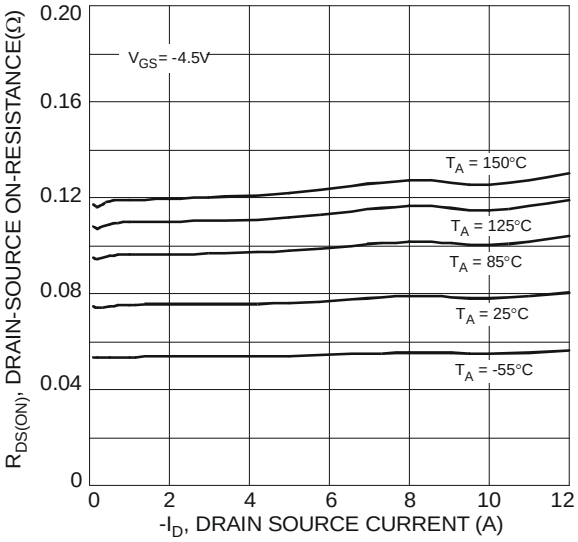


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

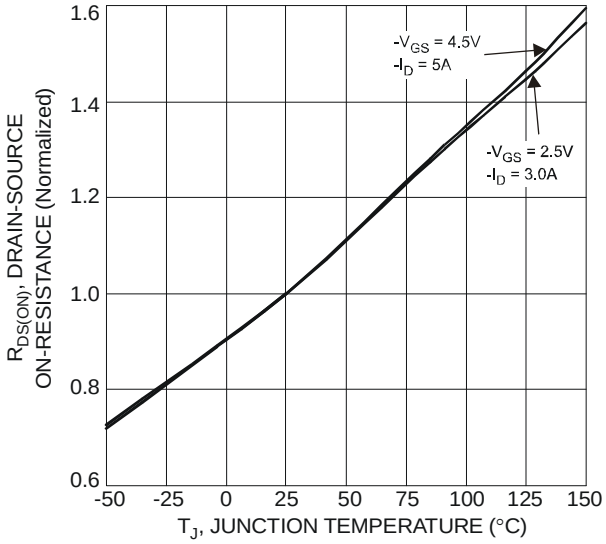


Fig. 5 On-Resistance Variation with Temperature

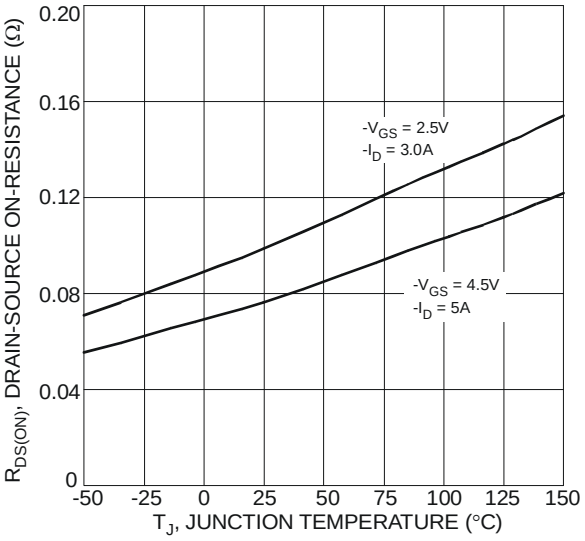


Fig. 6 On-Resistance Variation with Temperature

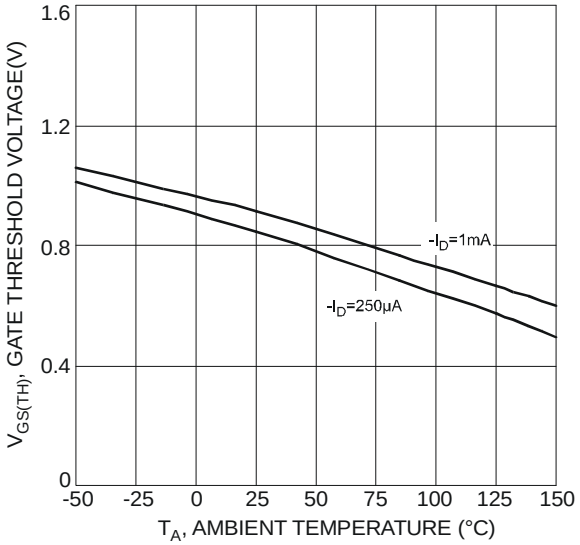


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

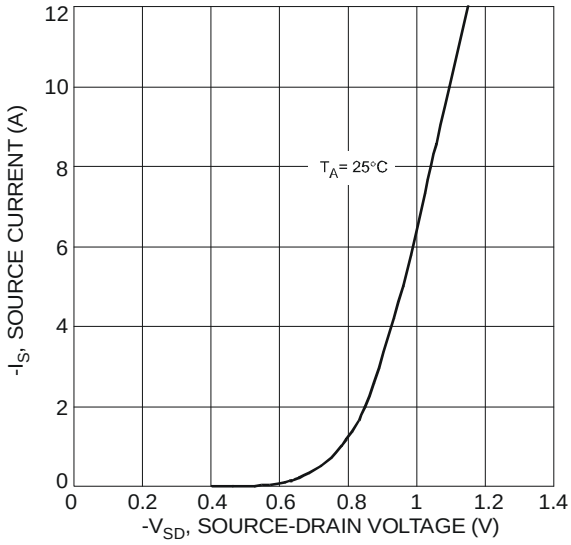


Fig. 8 Diode Forward Voltage vs. Current

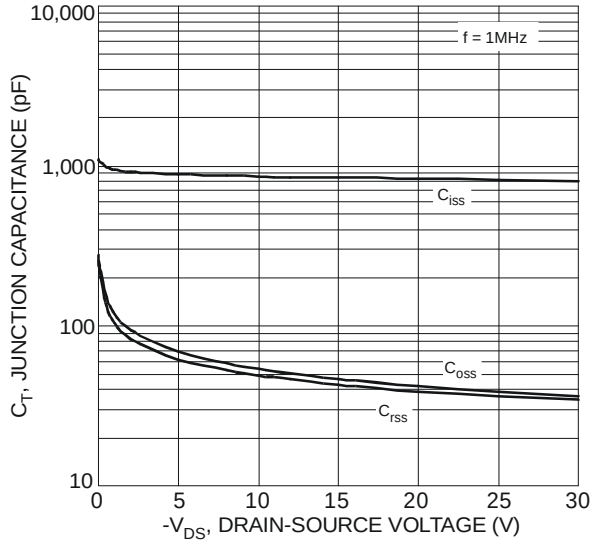


Fig. 9 Typical Junction Capacitance

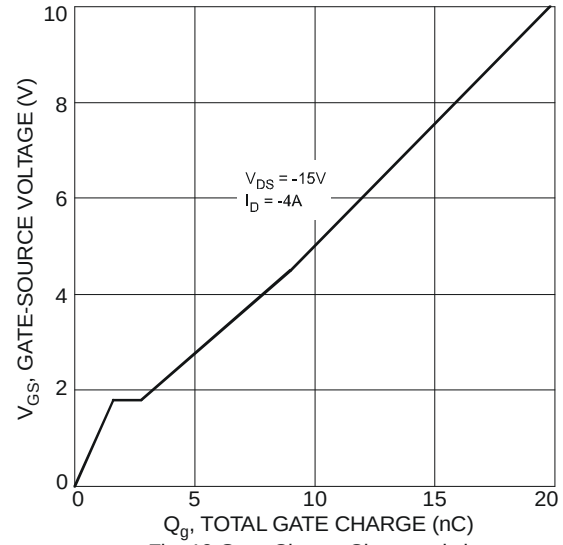


Fig. 10 Gate-Charge Characteristics

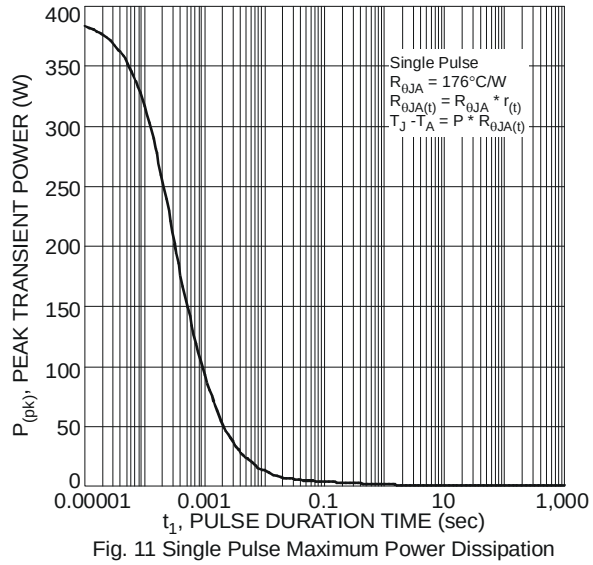


Fig. 11 Single Pulse Maximum Power Dissipation

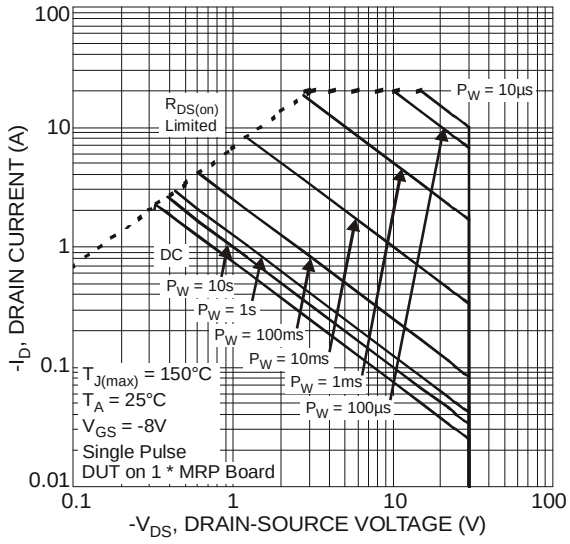


Fig. 12 SOA, Safe Operation Area

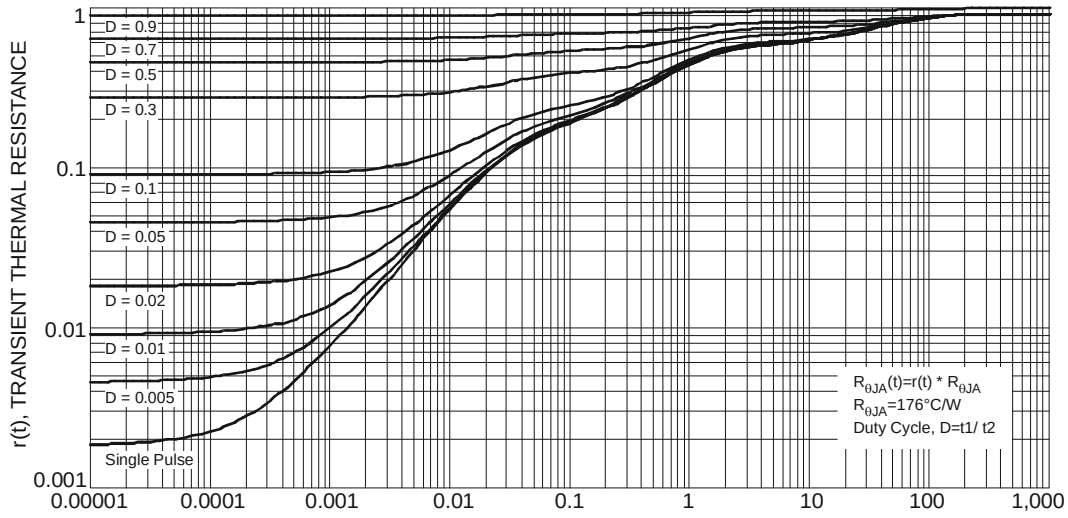
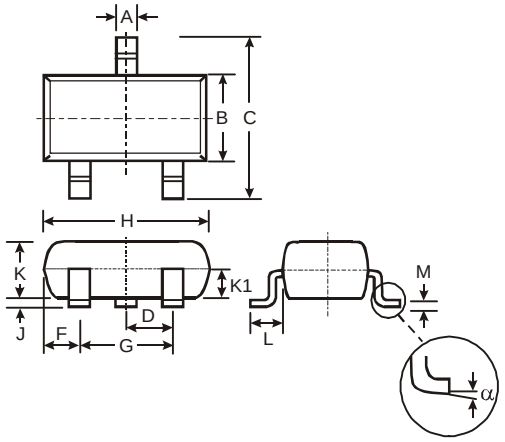


Fig. 13 Transient Thermal Resistance

Package Outline Dimensions

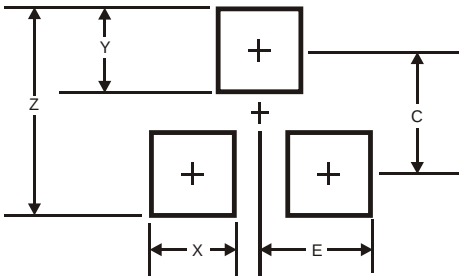
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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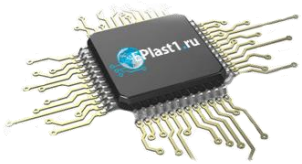
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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